SOT23-3 MOS

P- CHANNEL MOSFET in a SOT23-3 Plastic Package.

V_{DS} (V) = -12V

I_D = -6 A (V_{GS} = ±10V)

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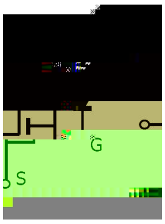
Power Management in Notebook computer, Portable Equipment and Battery powered systems.



PIN1 G PIN 2 S PIN 3 D

See Marking Instructions.

Marking	A3H

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-12	V
Gate-Source Voltage	V_{GSS}	±10	V
Continuous Drain Current	I_D (T_a=25°C)	-6	A
Continuous Drain Current	I_D (T_a=70°C)	-5.2	A
Pulsed Drain Current	I_{DM}	-20	A
Avalanche Current	I_{AS}	15.1	A
Avalanche energy L=0.5mH	E_{AS}	239.4	mJ
Power Dissipation for Single Operation	P		

+

m$6 0 44 0 52 /F8 1 Tf 0 0 0 sc 0 0 0 SC 0 Tr 40.285 56.236 TD [( )]TT56 0 44 0 S20 7

Parameter

[redacted]

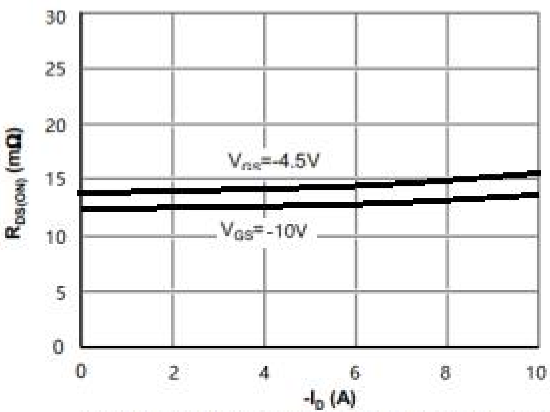


Figure 3: On-Resistance vs. Drain Current and Gate

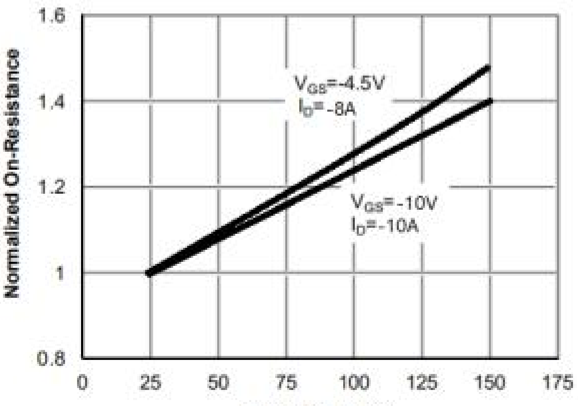
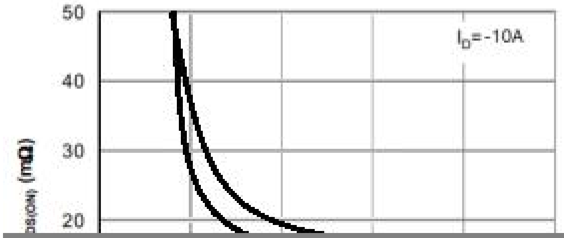
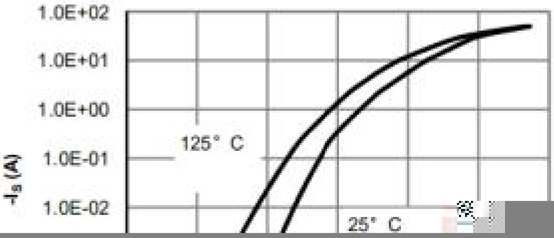


Figure 4: On-Resistanc

[redacted]





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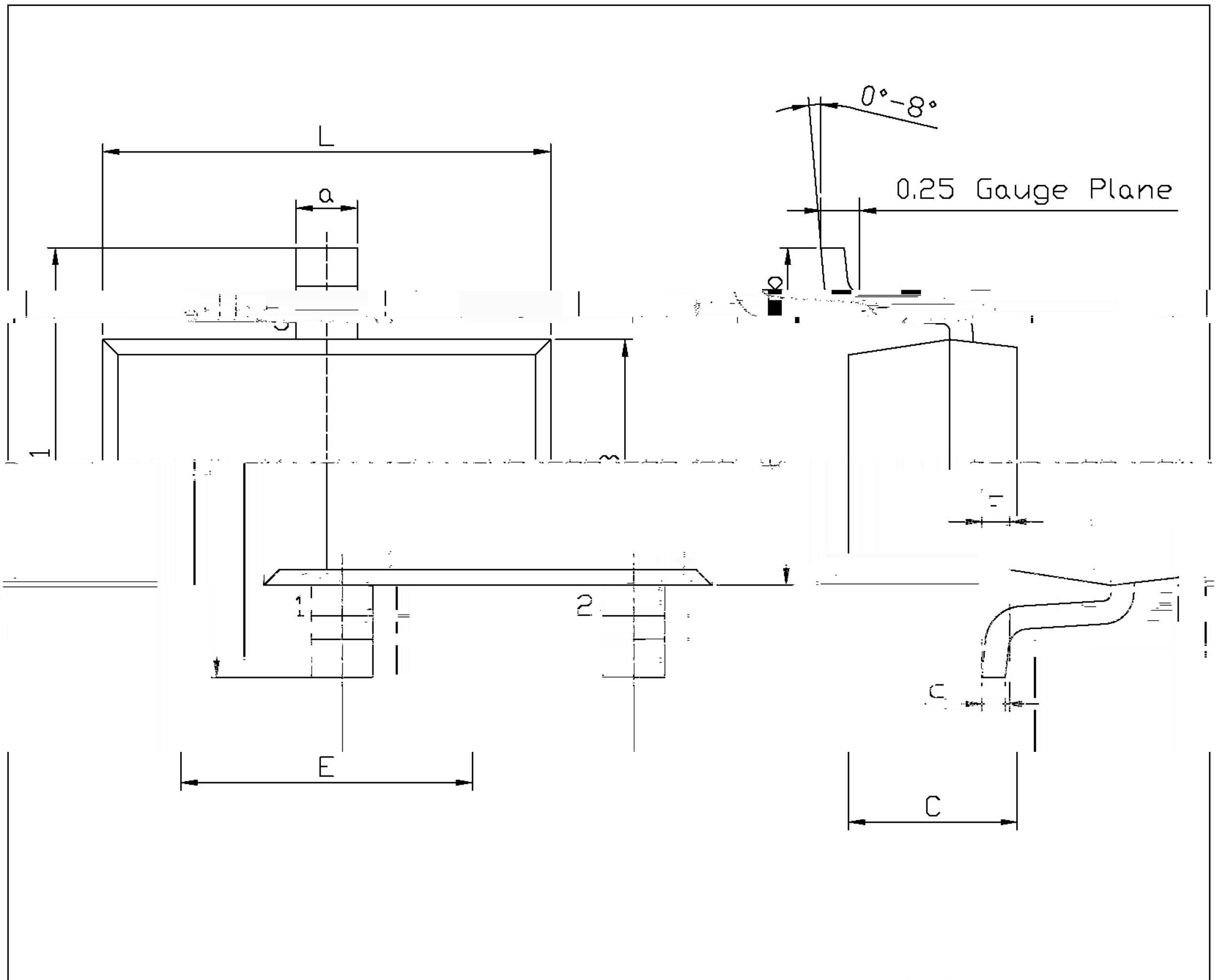
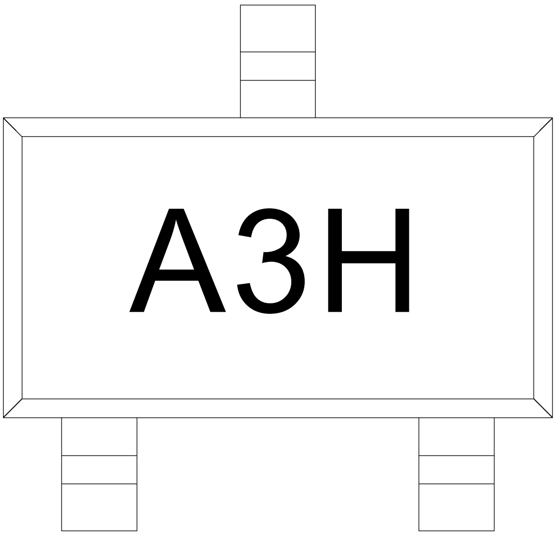


Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
[illegible]	0.35	0.50	[illegible]	2.82	3.02
[illegible]	[illegible]	[illegible]	[illegible]	[illegible]	[illegible]
[illegible]	[illegible]	[illegible]	[illegible]	[illegible]	[illegible]

[redacted]

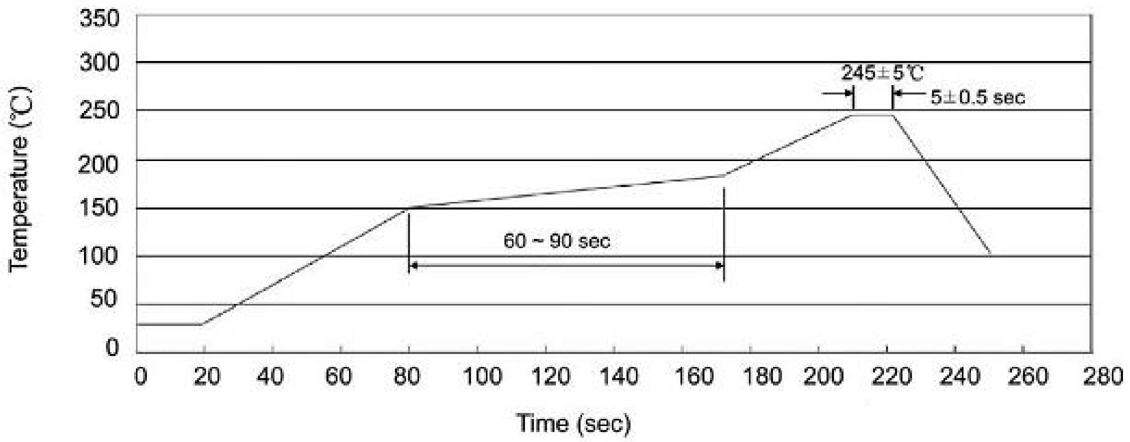


H:

A3:

Note:

H:	Company Code.
A3	Product Type



	Note:
1 150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2 245 5 5 0.5sec;	2.Peak Temp.:245 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260 5 10 1 sec. Temp.:260 5 Time:10 1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT23-3	3,000	10	30,000	4	120,000	7″ ×8	210×205×205	445×230×435